Hitachi Power Diodes
Status List

Date: Sep. 2020

Compliance status of RoHS directive

C:Compliant **S.C**:Compliant (Included RoHS exemption substance) **N**:Non compliant

Production Status

M:Mass production **O**:Order production **U**:Under development
W:Working sample **N**:Not recommend for new design **D**:Discontinued
E:Engineering sample

Load Dump Surge Suppressor Diodes

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	Production year	Production status
	P_{RSM} (kW)	V_{DC} (V)	T_j (°C)	Vz (V) Min.	Vz (V) Max.	Test Current (mA)				
ZSH5MA27(※)	3.0kW 62A	18	-40 ~+150	24.0	30.0	10	6A	S.C	2000	M
ZSH5MA27(A)(※)										
ZSH5MA27(S)(※)										
ZSH5MC27(※)	3.2kw 65A							S.C	2007	M
ZSH5MC27(S)(※)										
ZSH5MAZ27	3.4kW 70A	22						S.C	2009	M
ZSH5ME27							8	S.C	-	E
ZSH8MD27	5.7kW 130A						6B	S.C	2015	M
ZSH8MD40	5.7kW 80A	32		36.0	44.0	10		S.C	2015	M
ZSH5MT27C	3.4kW 70A	22		24.0	30.0	10	7A	S.C	2009	M
ZSH5MT27(Z)	4.3kW 90A									
ZSH5MT40C	4.3kW 62A	32		36.0	44.0	10				
ZSH5MT48C	4.3kW 50A	39		43.2	52.8	10				
ZSH5MT53C	4.3kW 45A	43		47.7	58.3	10				
ZSH5MV14	4.3kW 200A	11		13.0	15.0	10	5	S.C	2013	M
ZSH5MV27	4.3kW 100A	22		24.0	30.0	10			2012	

**** Please consider alternative new products as following.**

ZSH5MA27/27(A)/27(S) --> ZSH5MAZ27,ZSH5MT series,ZSH8MD27
ZSH5MC27/27(S) --> ZSH5MAZ27,ZSH5MT series,ZSH8MD27

Surge Suppressor Diodes

◆Surface Mount Type

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	Production year	Production status
	P_{RSM} (kW)	V_{RM} (V)	T_j (°C)	Vz (V) Min.	Vz (V) Max.	Test Current (mA)				
DAM1MB/2MB/3MB 12		9.7		11.4	12.7	1				
13		10.5		12.4	14.1	1				
15		12.1		13.5	15.6	1				
16		12.9		15.3	17.1	1				
18		14.5		16.8	19.1	1				
20		16.2		18.8	21.2	1				
22		17.8		20.8	23.3	1				
24		19.4		22.7	25.6	1				
27		21.8		25.1	28.9	1				
30	0.6/1.2/1.8	24.3	-65 ~+185	28.0	32.0	1	4A/4B/4C	S.C	2013	M
33		26.8		31.0	35.0	1				
36		29.1		33.4	38.6	1				
39		31.6		36.1	41.9	1				
43		34.8		39.8	46.2	1				
47		38.0		43.3	50.7	1				
51		41.3		46.9	55.1	1				
68		55.1		61.2	74.8	1				
75		60.7		67.5	82.5	1				
82		66.4		73.8	90.2	1				

Fast Recovery Diodes

◆Surface Mount Type

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	Production year	Production status
	V_{RRM} (V)	$I_{F(AV)}$ (A)	I_{FSM} (A)	T_j (°C)	V_{FM} (at I_{FM}) (V) (A)	t_{rr} (ns)				
DFM1MF2	200	1.0	25	-40 ~+150	0.95 (1.0)	35	4A	S.C	1997	M
DFM3MF2	200	3.0	50	-40 ~+150	0.95 (3.0)	35	4B	S.C	1997	M

High Voltage – Fast Recovery Diodes

◆Resin Molded Type

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	Production year	Production status
	V_{RRM} (kV)	* $I_{F(AV)}$ (mA)	I_{FSM} (A)	T_j (°C)	V_{FM} (at I_{FM}) (V) (mA)	t_{rr} (ns)				
DHM3T30	3	3 [15.75]	0.5	-40 ~+120	13 (5)	100	1B	S.C	1989	M
DHM3P40	4				13 (5)	100	1B	S.C	1989	M
DHM3G80	8				25 (5)	100	1F	S.C	1999	M
DHM3J120	12				42 (5)	100	1G	S.C	1999	M
DHM3C140	14				45 (5)	100	1H	S.C	1999	M
DHM3FJ60	6	1 [63] 3 [15.75]	0.5		22 (5)	70	1F	S.C	1999	M
DHM3FG80	8				28 (5)	70	1F	S.C	1999	M
DHM3UM80	8	1 [100] 3 [15.75]	0.5		23 (5)	40	1F	S.C	1998	M

* [ ] : Frequency, unit (kHz)

High Voltage – Fast Recovery Diodes (For Automotive)

◆Resin Molded Type

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	Production year	Production status
	V_{RRM} (kV)	$I_{F(AV)}$ (mA)	I_{FSM} (A)	T_j (°C)	V_{FM} (at I_{FM}) (V) (mA)	t_{rr} (ns)				
DHM10A30	3.0	10	1	+150	8.4 (10)	-	1K	S.C	2011	M
DHM30A10	1.0	30	3		2.0 (10)	-	1M	S.C	2013	M
DHM30A20	2.0	30	3		5.0 (10)	-	1M	S.C	2013	M
DHM30A25	2.5	30	3		5.0 (10)	-	1M	S.C	2014	M
DHM30A30	3.0	30	3		6.0 (10)	-	1F	S.C	2013	M
DHM30A40	4.0	30	3		10.0 (10)	-	1L	S.C	2011	M

High Voltage – Fast Recovery Diodes (For Automotive) Lead(Pb)-Free

◆Resin Molded Type

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	Production year	Production status
	V_{RRM} (kV)	$I_{F(AV)}$ (mA)	I_{FSM} (A)	T_j (°C)	V_{FM} (at I_{FM}) (V) (mA)	t_{rr} (ns)				
DHM30A10E	1.0	30	3	+150	2.0 (10)	-	1M	C	2017	M
DHM30A20E	2.0	30	3		5.0 (10)	-	1M	C	2017	M
DHM30A25E	2.5	30	3		5.0 (10)	-	1M	C	2016	M
DHM30A30E	3.0	30	3		6.0 (10)	-	1F	C	2017	M
DHM30A40E	4.0	30	3		10.0 (10)	-	1L	C	2017	M

Alternator Diodes

◆Super Low Loss Diodes

Type	Absolute maximum ratings		Characteristics			Outline	RoHS Status	Production year	Production status
	IF(AV) (A)	Tc (°C)	Vz (V) Min.	Vz (V) Max.	VFM (at IFM) (V) (A)				
MSM35C22	35	-40～+175	20	23	0.3 (100)	9A	S.C	-	W
MSM35C22R						9B			

◆Standard Type Diodes

Type	Absolute maximum ratings		Characteristics			Outline	RoHS Status	Production year	Production status
	IF(AV) (A)	Tj (°C)	Vz (V) Min.	Vz (V) Max.	VFM (at IFM) (V) (A)				
ZSM35C22	35	-40～+205	20	23	1.3 (100)	9A	S.C	2013	M
ZSM35C22R						9C			
ZSM50C22	50				1.2 (100)	9A		2012	M
ZSM50C22R						9C			
ZSM70A22	70 (Tc≦205℃)	-40～+225		24	1.2 (100)	9A		2013	M
ZSM70A22R	50 (Tc≦225℃)					9C			

Discontinued

◆General-Use Rectifier Diodes

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	Production year	Production status
	V_{RRM} (V)	$I_{F(AV)}$ (A)	I_{FSM} (A)	T_j (°C)	V_{FM} (at I_{FM}) (V) (A)	t_{rr} (ms)				
H14A	100	1.0	45	-40 ~+175	1.0 (1.0)	–	2A	S.C	1989	D *
B	200									
C	300									
D	400									
E	500									
F	600									
H	800			-40 ~+165						
J	1,000									
V06C	200	1.1	35	-65 ~+175	1.4 (1.1)	–	2A	S.C	1976	D *
E	400									
G	600									
J	800									
V03C	200	1.3	40		1.1 (1.3)	–	2A	S.C	1975	
E	400									
G	600									
J	800									
U05B	100	2.5	100		1.1 (2.5)	–	2B	S.C	1975	D *
C	200									
E	400									
G	600									
J	800									
U15B	100	3	80		1.0 (3.0)	–	2B	S.C	1978	D *
C	200									
E	400									
G	600		60							
J	800									

◆Zener Diodes

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	Production year	Production status
	P (W)	P_{RSM} (Wp)	T_j (°C)	Vz (V) Min.	Vz (V) Max.	Test Current (mA)				
AW01- 06	1.0	80	-40 ~+150	5.2	6.8	60	2A	S.C	1976	D *
AW01/AU01-07	1.0/2.5	80/160	-40 ~+150 / -40 ~+165	6.2	7.9	25/65	2A/2B	S.C / S.C	1976	D */ D *
08				7.7	8.7	25/65				
09				8.5	9.6	25/65				
10				9.4	10.6	25/65				
11				10.4	11.6	25/65				
12				11.4	12.7	25/65				
13				12.4	14.1	25/65				
15				13.5	15.6	15/40				
16				15.3	17.1	15/40				
18				16.8	19.1	15/40				
20				18.8	21.2	15/40				
22				20.8	23.3	15/40				
24				22.7	25.6	10/25				
27				25.1	28.9	10/25				
30				28.0	32.0	10/25				
33				31.0	35.0	10/25				

* EOL notices was issued in July 2018, Last buy order is closed in June 2019.

Discontinued

◆Fast Recovery Diodes

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	Production year	Production status
	V_{RRM} (V)	$I_{F(AV)}$ (A)	I_{FSM} (A)	T_j (°C)	V_{FM} (at I_{FM}) (V) (A)	t_{rr} (ms)				
DFG1D1	100	1.0	30	-65 ~+150	1.5 (1.0)	50ns	2A	S.C	1986	D *
2	200									
4	400									
DFG1C1	100	1.0	35		1.2 (1.0)	0.1	2A	S.C	1985	D *
2	200									
4	400									
6	600		30		1.6 (1.0)					
8	800									
DFG3A1	100	3.0	70		1.3 (3.0)	0.1	2B	S.C	1985	D *
2	200									
4	400									
V19B	100	1.0	30		1.2 (1.0)	0.2	2A	S.C	1977	D *
C	200									
E	400									
G	600									
DFG1A8	800	1.0	40	-65 ~+165	1.2 (1.0)	0.2	2A	S.C	1982	D *
H114B	200	1.0	40	-40 ~+150	1.15 (1.0)	0.2	2A	S.C	1989	D *
D	400									
E	500									
F	600									
U19B	100	2.5	80	-65 ~+150	1.3 (2.5)	0.2	2B	S.C	1978	D *
C	200									
E	400									
DFG2A6	600	2.5	80	-65 ~+165	1.3 (2.5)	0.2	2B	S.C	1982	D *
8	800									
V11J	800	0.4	30	-65 ~+150	2.5 (0.4)	0.4	2A	S.C	1975	D *
L	1,000									
M	1,300									
N	1,500									
V09C	200	0.8	35	-65 ~+165	1.6 (0.8)	0.4	2A	S.C	1975	D *
E	400									
G	600									
U07J	800	1.0	50	-65 ~+140	2.5 (1.0)	0.4	2B	S.C	1975	D *
L	1,000									
M	1,300									
N	1,500									
U06C	200	2.0	80	-65 ~+150	1.2 (2.0)	0.4	2B	S.C	1975	D *
E	400									
G	600									

◆Controlled Avalanche Diodes

Type	Absolute maximum ratings					Characteristics	Outline	RoHS Status	Production year	Production status
	V_{RRM} (V)	$I_{F(AV)}$ (A)	P_{RM} (W)	I_{FSM} (A)	T_j (°C)	V_{FM} (at I_{FM}) (V) (A)				
H24F	600	1.0	1,000	45	-65 ~+175	1.0 (1.0)	2A	S.C	1989	D *
H	800				-65 ~+165					
J	1,000									
V08E	400	1.1	40	35	-65 ~+175	1.4 (1.1)	2A	S.C	1975	D *
G	600									
J	800									
V07E	400	1.3	40	40		1.1 (1.3)	2A	S.C	1975	D *
G	600									
J	800									
V17A	50	1.3	1,500	50	-40 ~+165	1.1 (1.3)	2A	S.C	1975	D *
B	100									
C	200									
D	300									
E	400									
U17B	100	2.5	3,000	100	-40 ~+175	1.1 (2.5)	2B	S.C	1975	D *
C	200									
D	300									
E	400									

* EOL notices was issued in July 2018, Last buy order is closed in June 2019.

Discontinued

◆Surge Suppressor Diodes

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	Production status
	P_{RSM} (kW)	V_{DC} (V)	T_j (°C)	V_Z (V) Min.	V_Z (V) Max.	Test Current (mA)			
DAM1MA/3MA10	0.6/1.8	7	−40～+150	9.4	10.6	25/75	4A/4C	S.C	D
11		8		10.4	11.6	25/75			
12		9		11.4	12.7	25/75			D *
13		10		12.4	14.1	25/75			
15		11		13.5	15.6	25/75			
16		12		15.3	17.1	15/75			
18		13		16.8	19.1	15/45			
20		14		18.8	21.2	15/45			
22		16		20.8	23.3	15/45			
24		18		22.7	25.6	10/30			
27		20		25.1	28.9	10/30			
30		22		28.0	32.0	10/30			
33		24		31.0	35.0	10/30			
36		26		33.4	38.6	10/30			
39		28		36.1	41.9	10/20			
43		31		39.8	46.2	6/20			
47		34		43.3	50.7	6/20			
51		37		46.9	55.1	6/20			
68		49		61.2	74.8	4/10			
75		54		67.5	82.5	4/10			
82		59		73.8	90.2	3/10			

◆General-Use Rectifier Diodes

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	Production status
	V_{RRM} (V)	* $I_{F(AV)}$ (A)	I_{FSM} (A)	T_j (°C)	V_{FM} (at I_{FM}) (V) (A)	t_{rr} (ms)			
DSA3A1	100	3.0	120	-40~+150	1.0 (3.0)	-	2C	S.C	D *
2	200								
4	400								

◆General-Use Rectifier Diodes

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	Production status
	V_{RRM} (V)	* $I_{F(AV)}$ (A)	I_{FSM} (A)	T_j (°C)	V_{FM} (at I_{FM}) (V) (A)	t_{rr} (ms)			
DSM1MA1	100	1.0	25	-40 ~+150	1.1 (1.0)	-	4A	S.C	D *
2	200								
4	400								
DSM3MA1	100	3.0	80	-40 ~+150	1.0 (3.0)	-	4B	S.C	D *
2	200								
4	400								

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Discontinued

◆Surge Suppressor Diodes

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	Production status
	P_{RSM} (kW)	V_{DC} (V)	T_j (°C)	Vz (V) Min.	Vz (V) Max.	Test Current (mA)			
DAM1SA/1A10	0.6	7	-40 ~+150	9.4	10.6	25	1A/1B	S.C / S.C	D / D
11		8		10.4	11.6	25			
12		9		11.4	12.7	25			
13		10		12.4	14.1	25			
15		11		13.5	15.6	25			
16		12		15.3	17.1	15			
18		13		16.8	19.1	15			
20		14		18.8	21.2	15			
22		16		20.8	23.3	15			
24		18		22.7	25.6	10			
27		20		25.1	28.9	10			
30		22		28.0	32.0	10			
33		24		31.0	35.0	10			
36		26		33.4	38.6	10			
39		28		36.1	41.9	10			
43		31		39.8	46.2	6			
47		34		43.3	50.7	6			
51		37		46.9	55.1	6			
DAM3A/3B10	1.8	7	-40 ~+150	9.4	10.6	75	1E/1D	S.C / S.C	D / D
11		8		10.4	11.6	75			
12		9		11.4	12.7	75			
13		10		12.4	14.1	75			
15		11		13.5	15.6	75			
16		12		15.3	17.1	75			
18		13		16.8	19.1	45			
20		14		18.8	21.2	45			
22		16		20.8	23.3	45			
24		18		22.7	25.6	30			
27		20		25.1	28.9	30			
30		22		28.0	32.0	30			
33		24		31.0	35.0	30			
36		26		33.4	38.6	30			
39		28		36.1	41.9	30			
43		31		39.8	46.2	20			
47		34		43.3	50.7	20			
51		37		46.9	55.1	20			

◆High Voltage – Fast Recovery Diodes

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	Production status
	V_{RRM} (kV)	* $I_{F(AV)}$ (mA)	I_{FSM} (A)	T_j (°C)	V_{FM} (at I_{FM}) (V) (mA)	t_{rr} (ns)			
DHM3S20	2	3 [15.75]	0.5	-40 ~+120	10 (5)	100	1B	S.C	D
DHM3UG120	12	1 [100] 3 [15.75]			36 (5)	40	1G	S.C	D

*[ ]: Frequency,unit(kHz)

◆Load Dump Surge Suppressor Diodes

Type	Absolute maximum ratings			Characteristics			Outline	RoHS Status	Production status
	P_{RSM}(kW) I_{RSM}(A)	V_{DC} (V)	T_j (°C)	Vz (V) Min.	Vz (V) Max.	Iz (mA)			
ZSA5A27	3.0kW		-40 ~+150	24.0	30.0	10	3A	S.C	D
ZSA5MA27	62A						3B	S.C	D

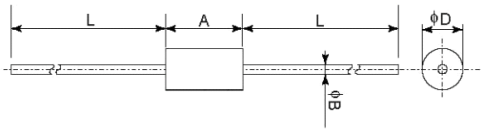
◆Fast Recovery Diodes

Type	Absolute maximum ratings				Characteristics		Outline	RoHS Status	Production status
	V_{RRM} (kV)	* $I_{F(AV)}$ (A)	I_{FSM} (A)	T_j (°C)	V_{FM} (at I_{FM}) (V) (A)	t_{rr} (ms)			
DFG1E 6	600	0.3	5	-65～+150	5.0(0.3)	35ns	2A	S.C	D
8	800								
10	1,000								

Outline

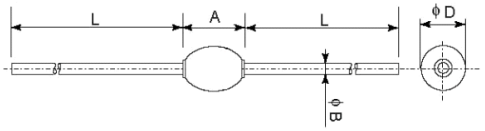
[Dimensions in mm]

●Outline No.1



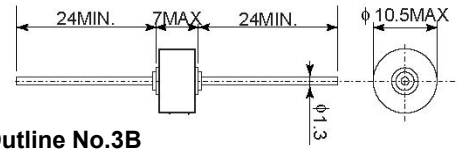
Items	A	ϕD	ϕB	L (Min.)
1A	3	2.5	0.6	28
1B	5	2.65	0.6	27
1C	5	2.65	0.8	27
1D	6	3.6	0.8	26
1E	7.5	6.4	1.2	26
1F	6.5	2.5	0.5	28
1G	10	2.5	0.5	26
1H	10	3	0.6	26,28
1J	8	3	0.6	28
1K	6.5	2.5	0.5	27
1L	8	3	0.6	27
1M	5	2.5	0.5	27

●Outline No.2

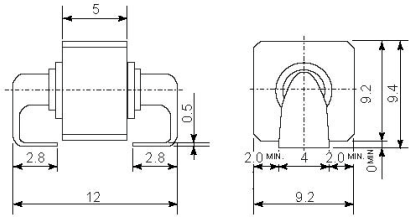


Items	A (Max.)	ϕD (Max.)	ϕB	L (Min.)
2A	5	3.5	0.8	29
2B	7	5	1.2	28
2C	7	5	1.2	27

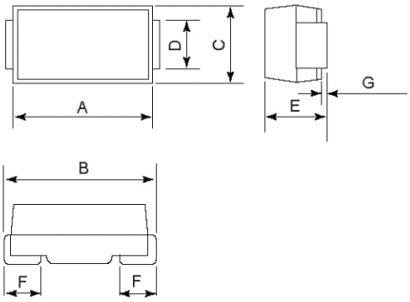
●Outline No.3A



●Outline No.3B

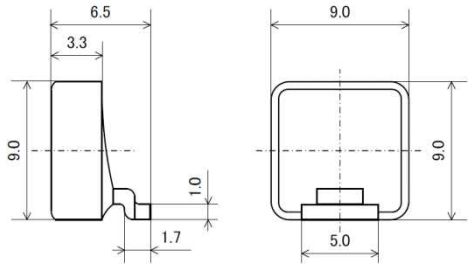


●Outline No.4

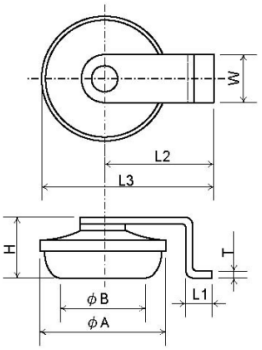


Items	A	B	C	D	E	F	G
4A	4.3	4.7	2.5	1.5	2.0	1.2	0.1
4B	4.4	5.4	3.6	2.0	2.3	1.2	0.2
4C	7.0	7.6	4.0	2.0	2.5	1.4	0.2

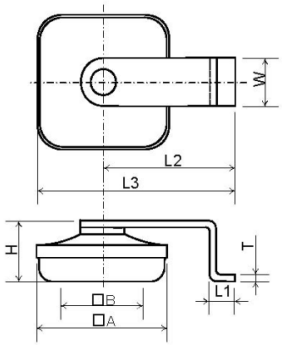
●Outline No.5



●Outline No.6



●Outline No.7A, 7B



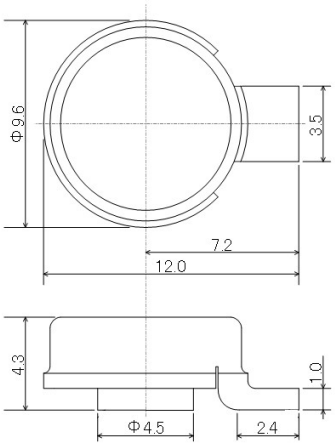
Items	A	B	L1	L2	L3	H	W	T
6A	9.6	7.4	2.0	8.3	13.1	4.4	3.5	0.5
6B*	9.6	-	2.0	8.3	13.1	6.0	3.5	0.5
7A	10.0	7.5	2.0	10.0	15.0	4.4	3.5	0.5
7B**	10.0	7.5	2.0	10.0	15.0	4.4	2.7	0.5

*:Packages is different　　**:JEDEC DO-218AB Compatible

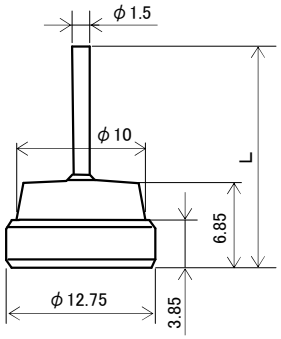
Outline

[Dimensions in mm]

●Outline No.8



●Outline No.9A, 9B, 9C



Items	L
9A	19.2
9B	28.5
9C	17.0

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